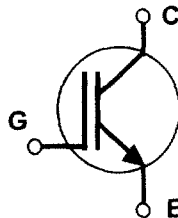


FEATURES

- * High Speed Switching
- * Low Saturation Voltage
: $V_{CE(sat)} = 2.1 \text{ V (@ } I_C = 3\text{A)}$
- * High Input Impedance

APPLICATIONS

- * AC & DC Motor controls
- * General Purpose Inverters
- * Robotics , Servo Controls
- * Power Supply
- * Lamp Ballast

D²-PAK

ABSOLUTE MAXIMUM RATINGS

Symbol	Characteristics	Rating	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_c = 25^\circ\text{C}$	6	A
	Collector Current @ $T_c = 100^\circ\text{C}$	3	A
$I_{CM(1)}$	Pulsed Collector Current	25	A
P_C	Maximum Power Dissipation @ $T_c = 25^\circ\text{C}$	30	W
	Maximum Power Dissipation @ $T_c = 100^\circ\text{C}$	12	W
T_j	Operating Junction Temperature	$-55 \sim 150$	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	$-55 \sim 150$	$^\circ\text{C}$
T_L	Maximum Lead Temp. For Soldering Purposes, $\frac{1}{8}$ " from case for 5 seconds	300	$^\circ\text{C}$

Notes:(1) Repetitive rating : Pulse width limited by max. junction temperature

ELECTRICAL CHARACTERISTICS

(T_c=25°C, Unless Otherwise Specified)

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Units
BV _{CES}	C - E Breakdown Voltage	V _{GE} = 0V, I _C = 250μA	600	-	-	V
ΔV _{CES} / ΔT _J	Temperature Coeff. of Breakdown Voltage	V _{GE} = 0V, I _C = 1mA	-	0.6	-	V/°C
V _{GE(th)}	G - E threshold voltage	I _C = 3mA, V _{CE} = V _{GE}	4.0	5.5	7.5	V
I _{CES}	Collector cutoff Current	V _{CE} = V _{CES} , V _{GE} = 0V	-	-	250	μA
I _{GES}	G - E leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	-	-	100	nA
V _{CE(sat)}	Collector to Emitter saturation voltage	I _C =3A, V _{GE} = 15V	-	2.1	2.6	V
		I _C =6A, V _{GE} = 15V	-	2.6	-	V
C _{ies}	Input capacitance	V _{GE} = 0V, f = 1MHz V _{CE} = 30V	-	220	-	pF
C _{oes}	Output capacitance		-	22	-	pF
C _{res}	Reverse transfer capacitance		-	7	-	pF
t _{d(on)}	Turn on delay time	V _{CC} = 300V, I _C = 3A V _{GE} = 15V R _G = 80 Ω Inductive Load	-	15	-	ns
t _r	Turn on rise time		-	22	-	ns
t _{d(off)}	Turn off delay time		-	40	70	ns
t _f	Turn off fall time		-	80	160	ns
E _{on}	Turn on Switching Loss		-	75	-	μJ
E _{off}	Turn off Switching Loss		-	30	-	μJ
E _{ts}	Total Switching Loss		-	100	125	μJ
Q _g	Total Gate Charge	V _{CC} = 300V	-	15	22	nC
Q _{ge}	Gate-Emitter Charge	V _{GE} = 15V	-	5	8	nC
Q _{gc}	Gate-Collector Charge	I _C = 3A	-	4	6	nC
L _e	Internal Emitter Inductance	Measured 5mm from PKG	-	7.5	-	nH

THERMAL RESISTANCE

Symbol	Characteristics	Min	Typ	Max	Units
$R_{\theta JC}$	Junction-to-Case	-	-	4.0	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)	-	-	40	$^{\circ}\text{C}/\text{W}$

2

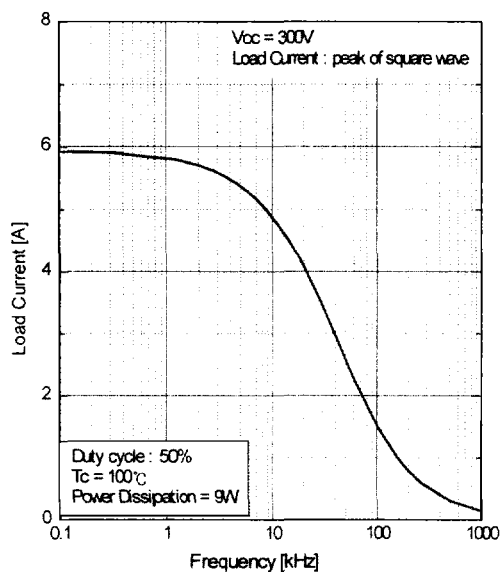


Fig.1 Typical Load Current vs. Frequency

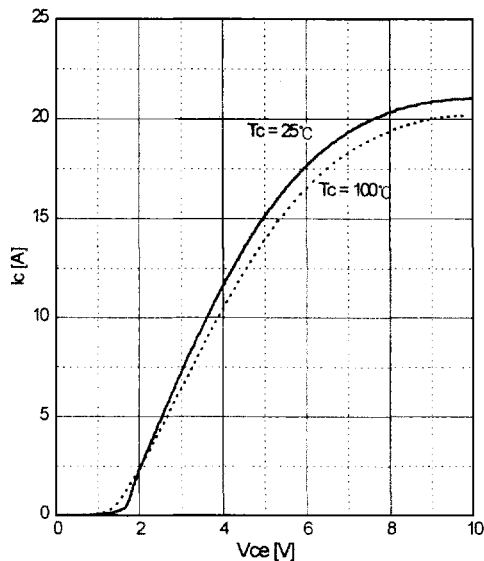


Fig.2 Typical Output Characteristics

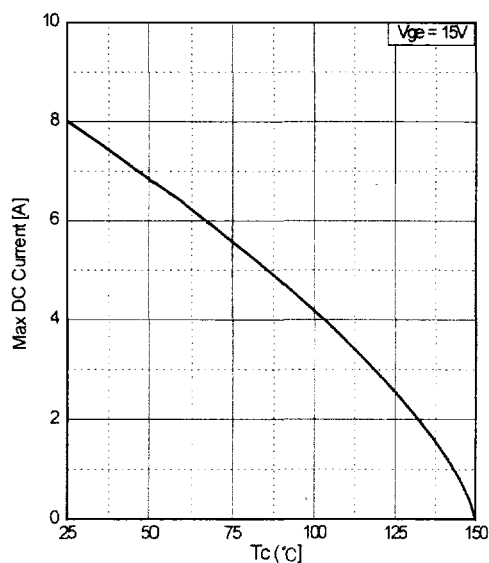


Fig.3 Maximum Collector Current vs. Case Temperature

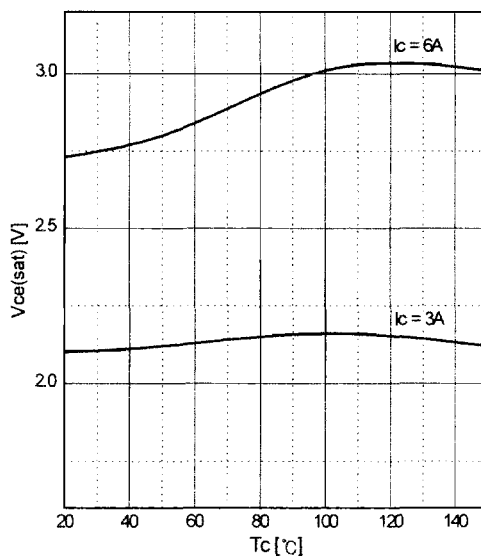


Fig.4 Collector to Emitter Voltage vs. Case Temperature

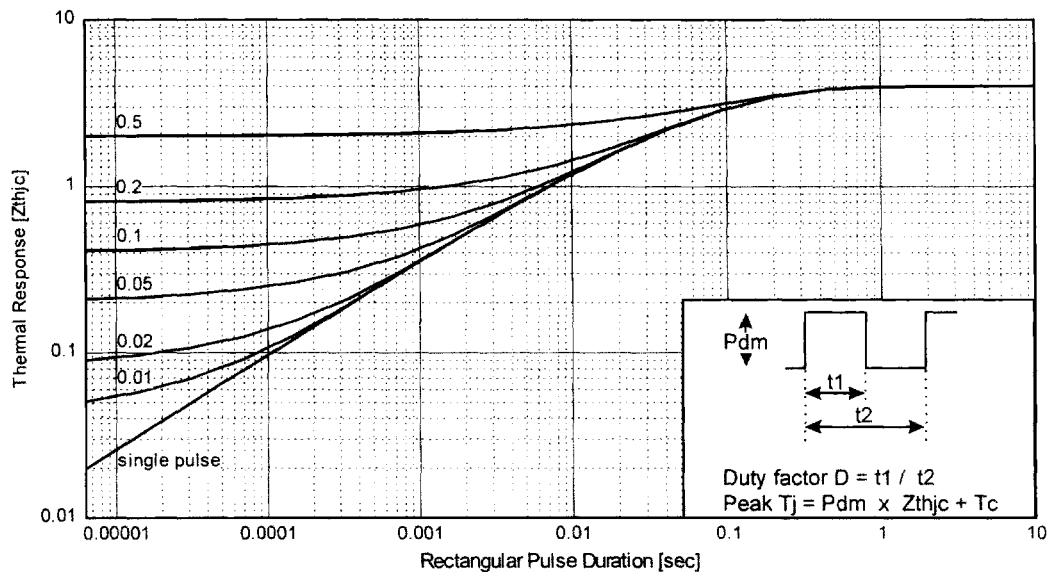


Fig.5 Maximum Effective Transient Thermal Impedance, Junction to Case

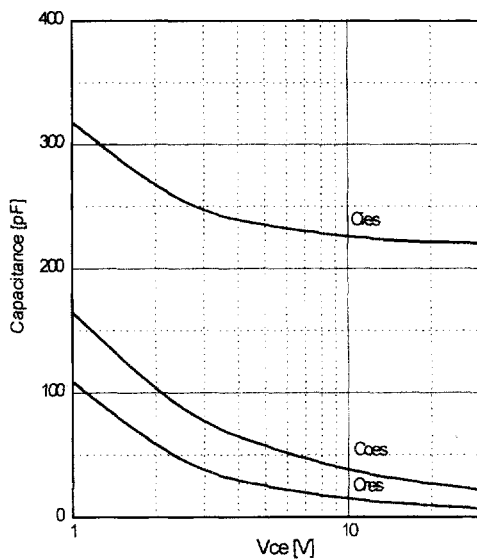


Fig.6 Typical Capacitance vs.
Collector to Emitter Voltage

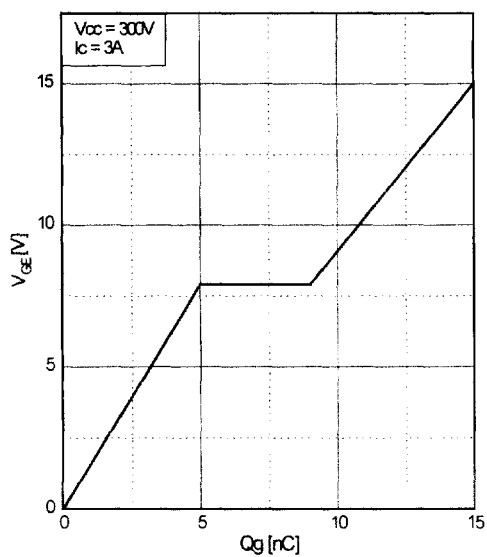


Fig.7 Typical Gate Charge vs.
Gate to Emitter Voltage

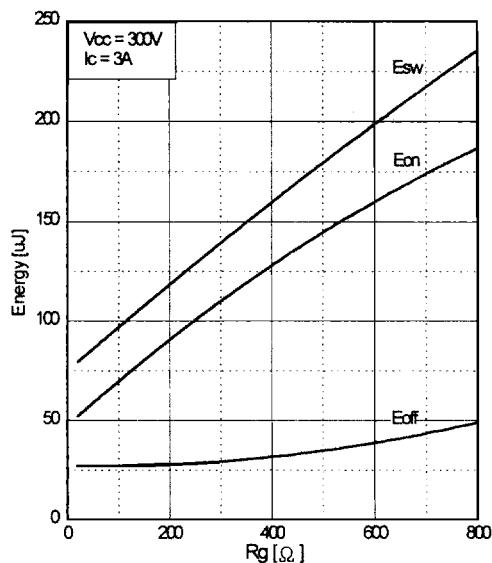


Fig.8 Typical Switching Loss vs. Gate Resistance

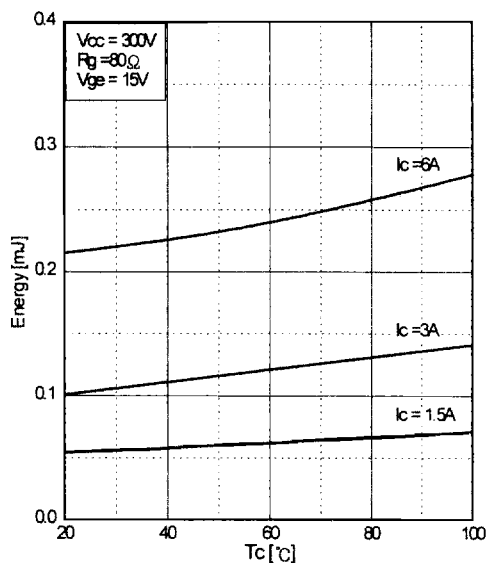


Fig.9 Typical Switching Loss vs. Case Temperature

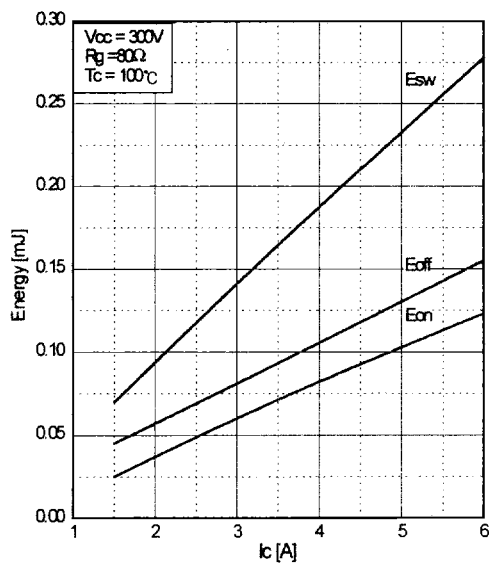


Fig.10 Typical Switching loss vs. Collector to Emitter Current

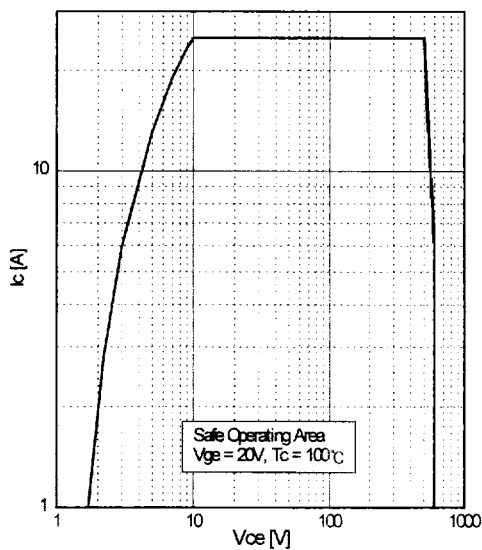


Fig.11 Turn-off SOA